

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC3279

Strobe Flash Applications
 Medium Power Amplifier Applications

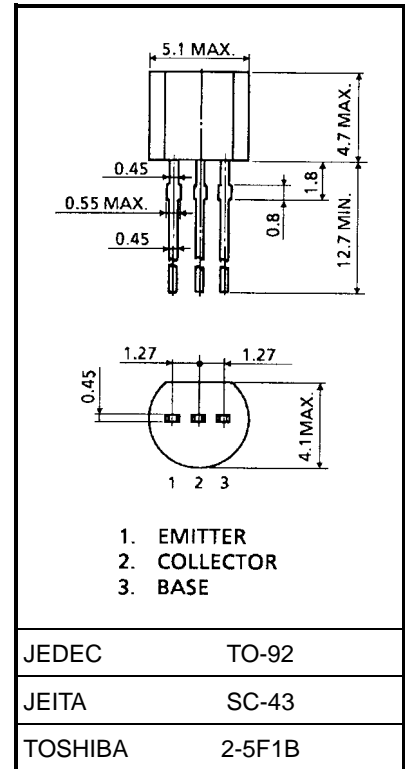
Unit: mm

- High DC current gain and excellent h_{FE} linearity
 : $h_{FE} (1) = 140\sim 600$ ($V_{CE} = 1\text{ V}$, $I_C = 0.5\text{ A}$)
 : $h_{FE} (2) = 70$ (min), 200 (typ.) ($V_{CE} = 1\text{ V}$, $I_C = 2\text{ A}$)
- Low saturation voltage: $V_{CE} (sat) = 0.5\text{ V}$ (max)
 ($I_C = 2\text{ A}$, $I_B = 50\text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	30	V
Collector-emitter voltage		V_{CES}	30	V
		V_{CEO}	10	
Emitter-base voltage		V_{EBO}	6	V
Collector current	DC	I_C	2	A
	Pulsed (Note 1)	I_{CP}	5	
Base current		I_B	0.2	A
Collector power dissipation		P_C	750	mW
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~150	$^\circ\text{C}$

Note 1: Pulse width = 10 ms (max), duty cycle = 30% (max)

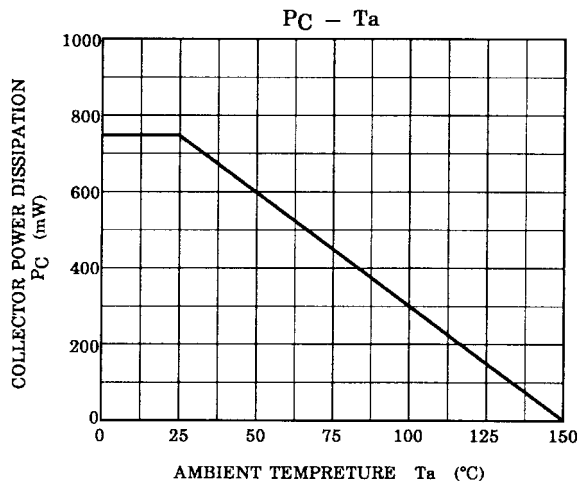
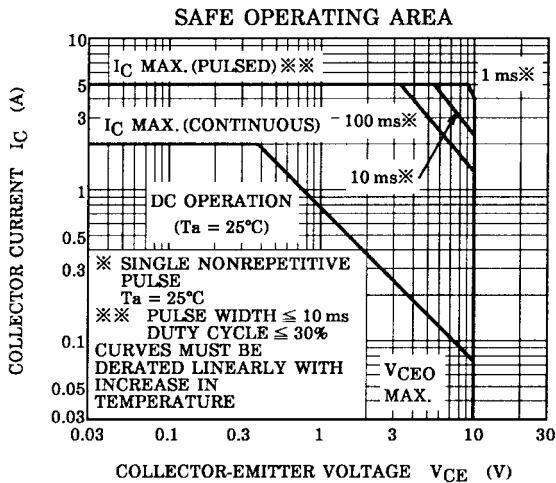
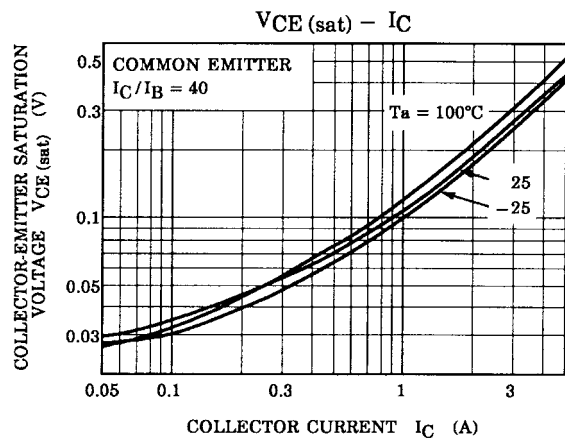
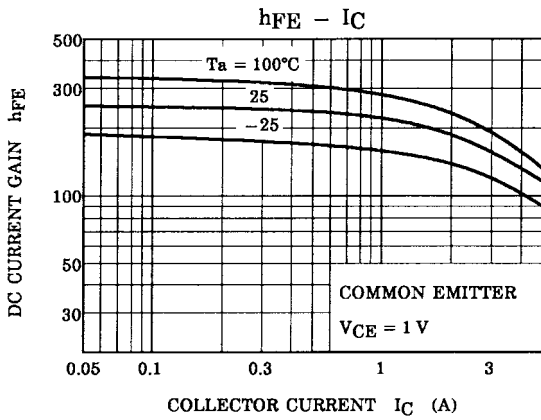
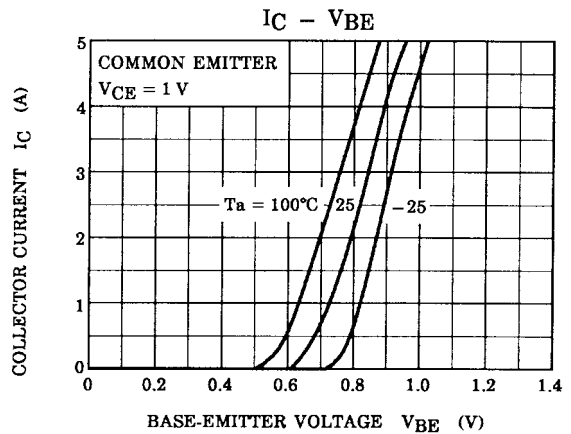
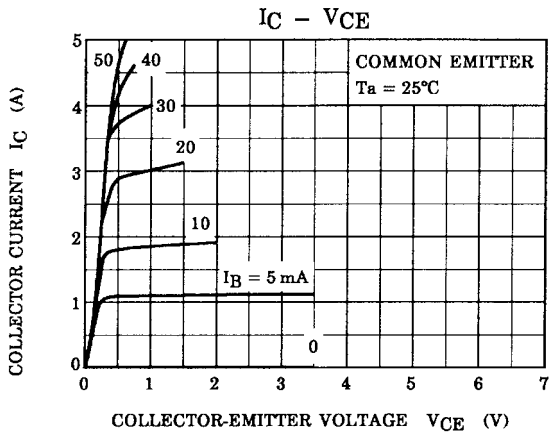


Weight: 0.21 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 30\text{ V}$, $I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6\text{ V}$, $I_C = 0$	—	—	0.1	μA
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = 10\text{ mA}$, $I_B = 0$	10	—	—	V
Emitter-base breakdown voltage	$V_{(BR) EBO}$	$I_E = 1\text{ mA}$, $I_C = 0$	6	—	—	V
DC current gain	$h_{FE} (1)$ (Note 2)	$V_{CE} = 1\text{ V}$, $I_C = 0.5\text{ A}$	140	—	600	
	$h_{FE} (2)$	$V_{CE} = 1\text{ V}$, $I_C = 2\text{ A}$	70	200	—	
Collector-emitter saturation voltage	$V_{CE} (sat)$	$I_C = 2\text{ A}$, $I_B = 50\text{ mA}$	—	0.2	0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1\text{ V}$, $I_C = 2\text{ A}$	—	0.86	1.5	V
Transition frequency	f_T	$V_{CE} = 1\text{ V}$, $I_C = 0.5\text{ A}$	—	150	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	—	27	—	pF

Note 2: $h_{FE} (1)$ classification L: 140~240, M: 200~330, N: 300~450, P: 420~600



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